

July 2013

FDP120N10

N-Channel PowerTrench[®] MOSFET 100 V, 74 A, 12 m Ω

Features

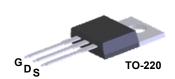
- $R_{DS(on)}$ = 9.7 m Ω (Typ.)@ V_{GS} = 10 V, I_D = 74 A
- · Fast Switching Speed
- · Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\mbox{\footnotesize{DS(on)}}}$
- · High Power and Current Handling Capability
- · RoHS Compliant

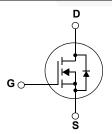
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor[®]'s advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- · Battery Protection Circuit
- · Motor Drives and Uninterruptible Power Supplies
- · Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted

Symbol		Parameter		FDP120N10	Unit	
V _{DSS}	Drain to Source Voltage	Orain to Source Voltage			V	
V _{GSS}	Gate to Source Voltage			±20	V	
	Drain Current	-Continuous (T _C = 25°C)		74	Δ.	
ID.	Drain Current	-Continuous (T _C = 100°C)		52	Α	
I _{DM}	Drain Current	- Pulsed	(Note 1)	296	Α	
E _{AS}	Single Pulsed Avalanche	Energy	(Note 2)	198	mJ	
dv/dt	Peak Diode Recovery dv	/dt	(Note 3)	6.0	V/ns	
D	Dawer Dissination	$(T_C = 25^{\circ}C)$		170	W	
P_{D}	Power Dissipation	- Derate above 25°C		1.14	W/°C	
T _J , T _{STG}	Operating and Storage To	emperature Range		-55 to +175	οС	
T _L	Maximum Lead Tempera 1/8" from Case for 5 Sec	ture for Soldering Purpose, onds		300	°C	

Thermal Characteristics

Symbol	Parameter	FDP120N10	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Case, Max.	0.88	
$R_{\theta CS}$	Thermal Resistance, Case to Sink Typ.	0.5	°C/W
$R_{\theta JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	

Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity
FDP120N10	FDP120N10	TO-220	-	-	50

Electrical Characteristics $T_C = 25^{\circ}C$ unless otherwise noted

Symbol	Parameter Test Conditions		Min.	Тур.	Max.	Unit
Off Charac	eteristics					
BV_{DSS}	Drain to Source Breakdown Voltage	$I_D = 250 \mu A, V_{GS} = 0 V, T_C = 25^{\circ} C$	100	-	-	V
$\frac{\Delta BV_{DSS}}{\Delta T_{J}}$	Breakdown Voltage Temperature Coefficient	I _D = 250μA, Referenced to 25°C	-	0.1	-	V/°C
1	Zero Gate Voltage Drain Current	V _{DS} = 100V, V _{GS} = 0V	-	-	1	^
IDSS	Zero Gate Voltage Drain Current	$V_{DS} = 100V, V_{GS} = 0V, T_{C} = 150^{\circ}C$	-	-	500	μΑ
I _{GSS}	Gate to Body Leakage Current	$V_{GS} = \pm 20V, V_{DS} = 0V$	-	-	±100	nA

On Characteristics

$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \mu A$	2.5	-	4.5	V
R _{DS(on)}	Static Drain to Source On Resistance	V _{GS} = 10V, I _D = 74A	-	9.7	12	mΩ
9 _{FS}	Forward Transconductance	V _{DS} = 10V, I _D = 74A	-	105	-	S

Dynamic Characteristics

C _{iss}	Input Capacitance)/ OF)/)/ O)/	-	4215	5605	pF
C _{oss}	Output Capacitance	$V_{DS} = 25V, V_{GS} = 0V$ f = 1MHz	-	405	540	pF
C _{rss}	Reverse Transfer Capacitance	1 111112	-	170	255	pF
Q _{g(tot)}	Total Gate Charge at 10V		-	66	86	nC
Q_{gs}	Gate to Source Gate Charge	$V_{DS} = 80V I_{D} = 74A$	-	26	-	nC
Q_{gd}	Gate to Drain "Miller" Charge	$V_{GS} = 10V$ (Note 4)	-	20	-	nC

Switching Characteristics

	•						
t _{d(on)}	Turn-On Delay Time			-	27	64	ns
t _r	Turn-On Rise Time	$V_{DD} = 50V, I_{D} = 74A$		-	105	220	ns
t _{d(off)}	Turn-Off Delay Time	$V_{GS} = 10V, R_{GEN} = 4.7\Omega$	2	-	39	88	ns
t _f	Turn-Off Fall Time		(Note 4)	-	15	40	ns

Drain-Source Diode Characteristics

I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	74	Α
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		/ -	-	296	Α
V_{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _{SD} = 74A	-	-	1.3	V
t _{rr}	Reverse Recovery Time	V _{GS} = 0V, I _{SD} = 74A	-	44	/-	ns
Q _{rr}	Reverse Recovery Charge	$dI_F/dt = 100A/\mu s$	-	67	_	nC

Notes:

- Repetitive Rating: Pulse width limited by maximum junction temperature
- 2. L = 0.11mH, I $_{AS}$ = 60A, V $_{DD}$ = 50V, R_{G} = 25 $\!\Omega,$ Starting T $_{J}$ = 25 $^{\circ}C$
- 3. $I_{SD} \le 74A$, di/dt $\le 200A/\mu s$, $V_{DD} \le BV_{DSS}$, Starting T_J = 25°C
- 4. Essentially Independent of Operating Temperature Typical Characteristics

Typical Performance Characteristics

Figure 1. On-Region Characteristics

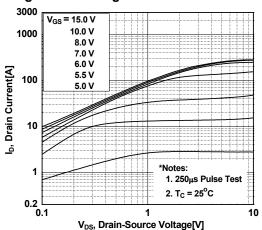


Figure 3. On-Resistance Variation vs.
Drain Current and Gate Voltage

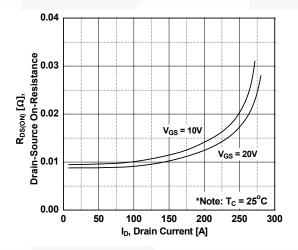


Figure 5. Capacitance Characteristics

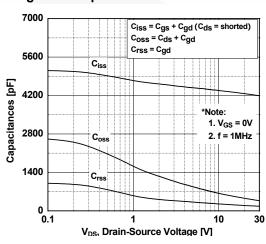


Figure 2. Transfer Characteristics

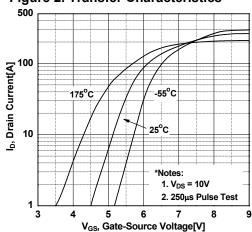


Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperature

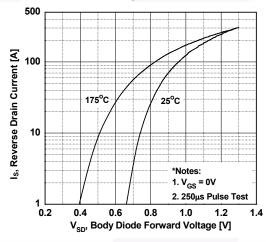
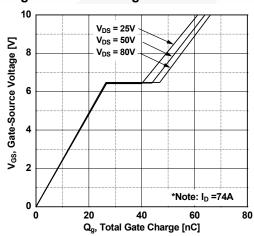


Figure 6. Gate Charge Characteristics



Typical Performance Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

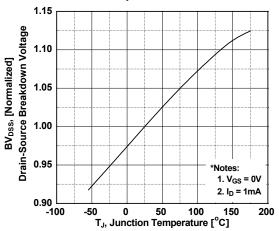


Figure 8. On-Resistance Variation vs. Temperature

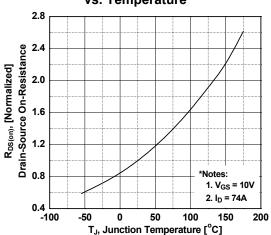


Figure 9. Maximum Safe Operating Area

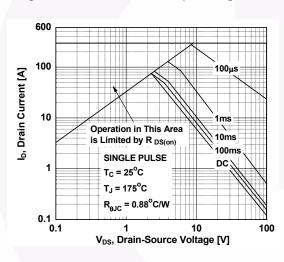


Figure 10. Maximum Drain Current vs. Case Temperature

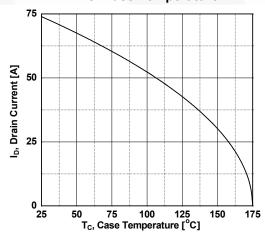


Figure 11. Transient Thermal Response Curve

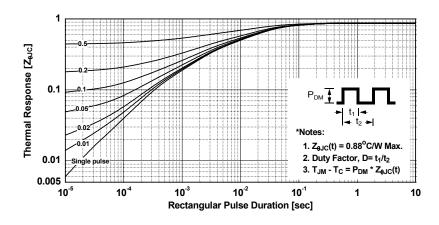


Figure 12. Gate Charge Test Circuit & Waveform

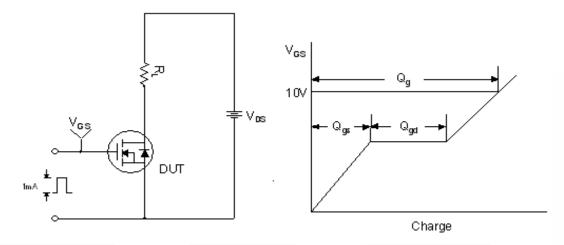


Figure 13. Resistive Switching Test Circuit & Waveforms

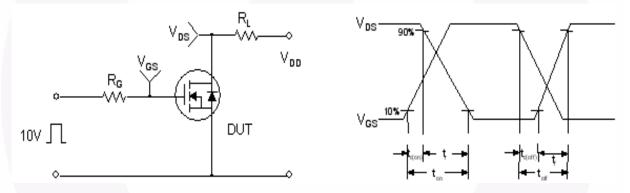
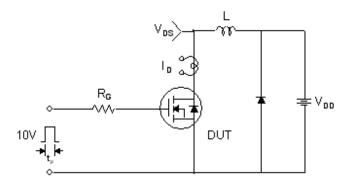
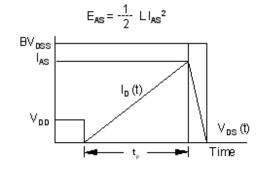


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms





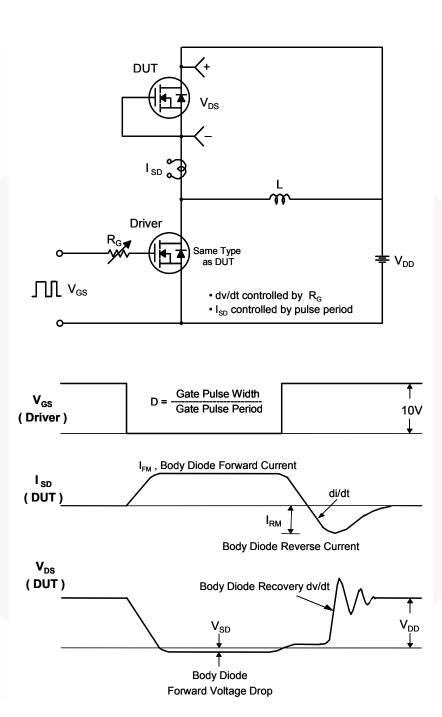


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

Physical Dimensions

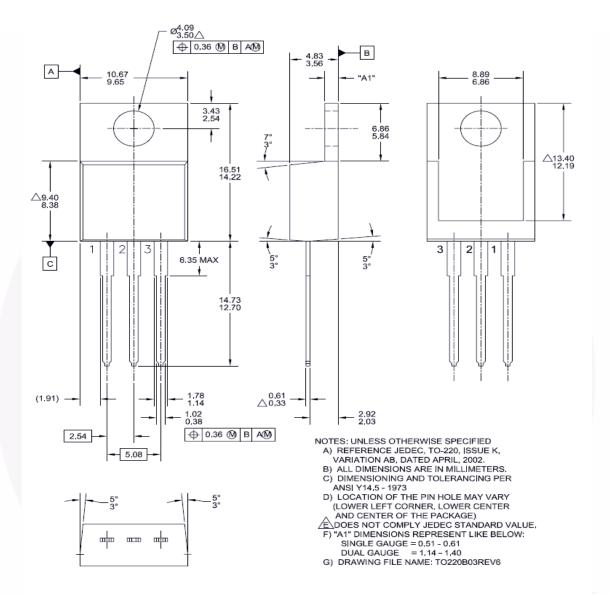


Figure 16. TO-220, MOLDED, 3LEAD, JEDEC VARIATION AB

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